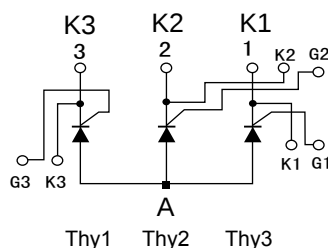
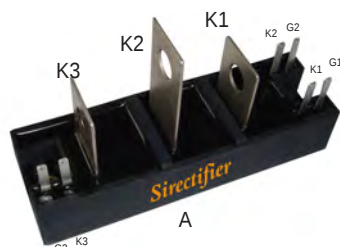
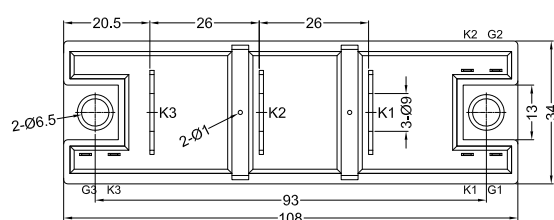
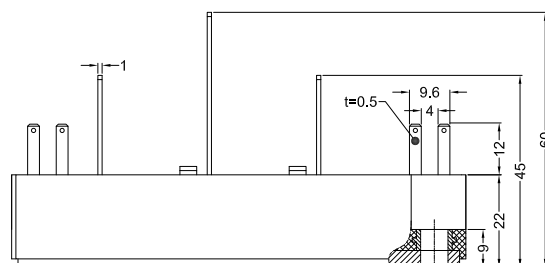


3TA152GK06NB

Three Phase Thyristor Module (Half Bridge)



Dimensions in mm (1mm = 0.0394")



Type	V _{RSM} V	V _{RRM} V
3TA152GK03NB	400	300
3TA152GK04NB	500	400
3TA152GK06NB	700	600



Symbol	Test Conditions	Maximum Ratings	Unit
I _{T(AV)} I _{T(RMS)}	Single phase, half wave, 180°C conduction, T _c =121°C	150 230	A
I _{TSM}	1/2cycle, 50Hz/60Hz, peak value, non-repetitive	3000/3400	A
I ² t		38000	A ² s
P _{GM} P _{G(AV)}		5 0.5	W
I _{FGM}		2	A
V _{FGM} V _{RGM}		10 5	V
di/dt	I _G =200mA, T _j =25°C, V _D =1/2V _{DRM} , di _G /dt=1A/us	400	A/us
T _{vJ} T _{vJM} T _{stg}		-40...+150 150 -40...+125	°C
M _s M _t	to heatsink M6 to terminals M8	1.96 ~ 2.94 2.50 ~ 5.00	Nm
Weight		200	g



3TA152GK06NB

Three Phase Thyristor Module (Half Bridge)

Symbol	Test Conditions	min.	typ.	max.	Unit
I_{DRM} I_{RRM}	at V _{DRM} , single phase, half wave, T _j =150°C			40 40	mA
V_{TM}	On-State Current 450A, T _j =25°C Inst. measurement			1.20	V
I_{GT}	T _j =25°C, I _T =1A, V _D =6V			150	mA
V_{GD}	T _j =150°C, V _D =1/2V _{DRM}			0.25	V
t_{gt}	I _T =200A, I _G =200mA, T _j =25°C, V _D =1/2V _{DRM} , dI _G /dt=1A/us			10	us
dv/dt	T _j =150°C, V _D =2/3V _{DRM} , Exponential wave		1000		V/us
I_H	T _j =25°C			70	mA
R_{thJC}	Junction to case (1/3 Module)			0.15	°C/W

FEATURES

- * International standard package
- * Copper base plate
- * Glass passivated chips
- * Center Gate chips with Higher di/dt
- * RoHS compliant

APPLICATIONS

- * Welding Machine Power Supply
- * DC Power Supply

ADVANTAGES

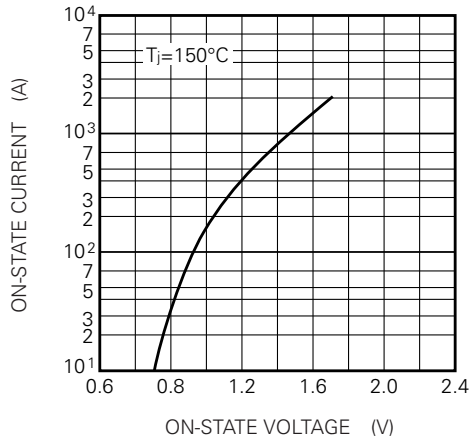
- * Space and weight savings
- * Simple mounting with two screws
- * Improved temperature and power cycling
- * Reduced protection circuits

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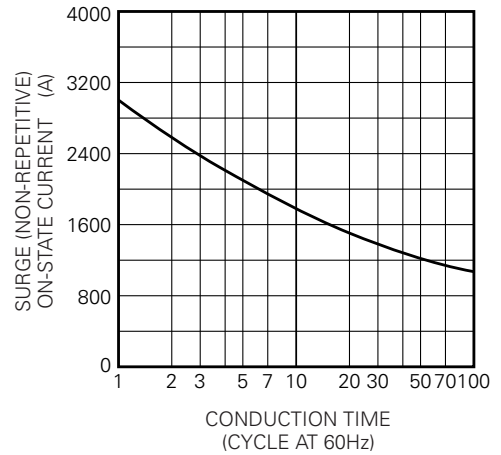
3TA152GK06NB

Three Phase Thyristor Module (Half Bridge)

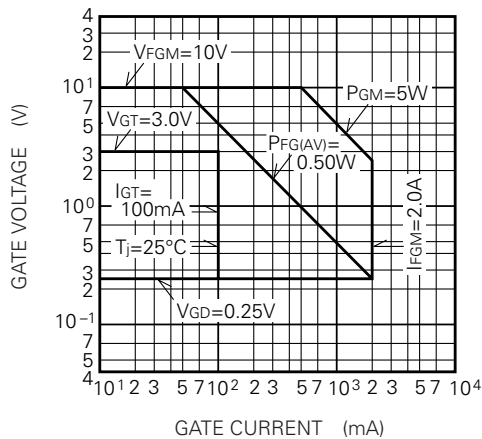
MAXIMUM ON-STATE CHARACTERISTIC



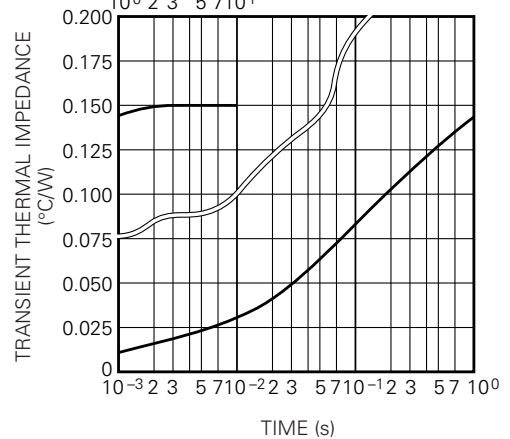
RATED SURGE (NON-REPETITIVE) ON-STATE CURRENT



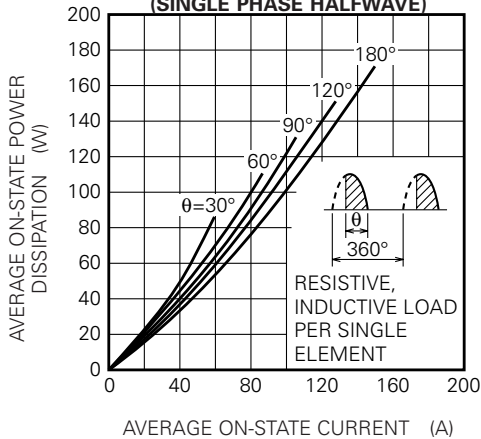
GATE CHARACTERISTICS



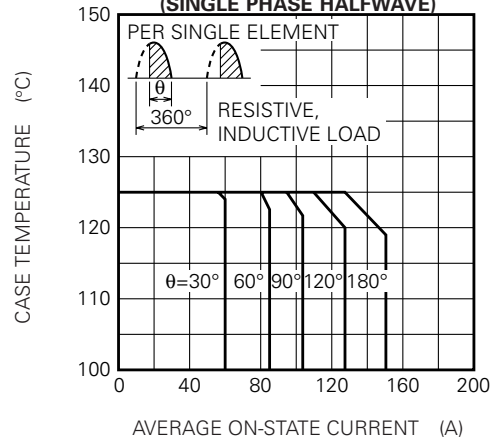
MAXIMUM TRANSIENT THERMAL IMPEDANCE (JUNCTION TO CASE)



MAXIMUM AVERAGE ON-STATE POWER DISSIPATION (SINGLE PHASE HALFWAVE)



LIMITING VALUE OF THE AVERAGE ON-STATE CURRENT (SINGLE PHASE HALFWAVE)



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